ROHM SH8MA2

30V Nch+Pch Power MOSFET

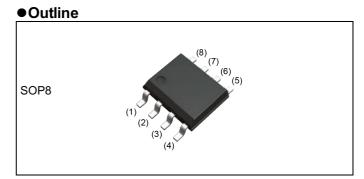
Symbol	Tr1:Nch	Tr2:Pch
V <sub>DSS</sub>	30V	-30V
R <sub>DS(on)</sub> (Max.)	80mΩ	82mΩ
I <sub>D</sub>	±4.5A	±4.5A
PD	2.7	7W

#### Features

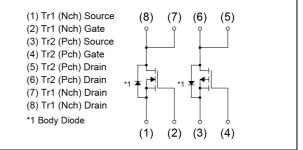
- 1) Low on resistance
- 2) Small Surface Mount Package (SOP8)
- 3) Pb-free lead plating ; RoHS compliant
- 4) Halogen Free

Application

Switching



#### Inner circuit



#### Packaging specifications

	Packing	Embossed Tape
	Reel size (mm)	330
Туре	Tape width (mm)	12
	Basic ordering unit (pcs)	2500
	Taping code	ТВ
	Marking	SH8MA2

#### • Absolute maximum ratings (T<sub>a</sub> = 25°C ,unless otherwise specified)

Deremeter	Currence of	Va	lue	Linit
Parameter	Symbol	Tr1:Nch	Tr2:Pch	Unit
Drain - Source voltage	V <sub>DSS</sub>	30	-30	V
Continuous drain current	Ι <sub>D</sub> *1	±4.5	±4.5	А
Pulsed drain current	I_DP*2	±12	±12	А
Gate - Source voltage	V <sub>GSS</sub>	±20	±20	V
Avalanche current, single pulse	I <sub>AS</sub> *3	4.0	-4.0	А
Avalanche energy, single pulse	E <sub>AS</sub> *3	1.1	1.4	mJ
	P <sub>D</sub> <sup>*1</sup>	2	.7	
Power dissipation (total)	P <sub>D</sub> *4	2	.0	W
	P <sub>D</sub> *5	1	.4	
Junction temperature	Tj	1:	50	°C
Operating junction and storage temperature range	T <sub>stg</sub>	-55 to	+150	C°

#### •Thermal resistance

Deremeter	Currence of		Values		Linit
Parameter	Symbol	Min.	Тур.	Max.	Unit
Thermal registered innetion embient (total)	$R_{thJA}^{*4}$	-	-	62.5	°c/W
Thermal resistance, junction - ambient (total)	$R_{thJA}^{*5}$	-	-	89.2	C/VV

### •Electrical characteristics (T<sub>a</sub> = 25°C)

Demonster	Oursels al	<b>T</b>	O and lititized		Values		1.114
Parameter	Symbol	Туре	Conditions	Min.	Тур.	Max.	Unit
Drain - Source breakdown	V	Tr1	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA	30	-	-	M
voltage	V <sub>(BR)DSS</sub>	Tr2	V <sub>GS</sub> = 0V, I <sub>D</sub> = -1mA	-30	-	-	V
Breakdown voltage	∆V <sub>(BR)DSS</sub>	Tr1	I <sub>D</sub> = 1mA, referenced to 25°C	-	21	-	m)//°0
temperature coefficient	$\Delta T_j$	Tr2	$I_D = -1 \text{ mA}$ , referenced to 25°C	-	-22	-	mV/°C
Zero gate voltage		Tr1	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V	-	-	1	
drain current	I <sub>DSS</sub>	Tr2	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V	-	-	-1	μA
Gate - Source		Tr1	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V	-	-	±100	
leakage current	I <sub>GSS</sub>	Tr2	$V_{DS}$ = 0V, $V_{GS}$ = ±20V	-	-	±100	nA
Gate threshold	V	Tr1	$V_{DS} = V_{GS}, I_D = 1mA$	1.0	-	2.5	V
voltage	V <sub>GS(th)</sub>	Tr2	$V_{DS} = V_{GS}, I_D = -1mA$	-1.0	-	-2.5	V
Gate threshold voltage	$\Delta V_{GS(th)}$	Tr1	I <sub>D</sub> = 1mA, referenced to 25°C	-	-3	-	mV/°C
temperature coefficient	ΔTj	Tr2	I <sub>D</sub> = -1mA, referenced to 25°C	-	2.9	-	mv/ C
		Tr1	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.5A	-	57	80	
Static drain - source	<b>D</b> *6	ILL	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4.0A	-	88	125	
on - state resistance	R <sub>DS(on)</sub> *6	Tr2	V <sub>GS</sub> = -10V, I <sub>D</sub> = -4.5A	-	63	82	mΩ
		112	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -4.0A	-	89	115	
Gate resistance	D	Tr1	f=1MHz open drain	-	3.5	-	Ω
	R <sub>G</sub>	Tr2	f=1MHz, open drain	-	13	-	
Forward Transfer	IV- 1*6	Tr1	V <sub>DS</sub> = 5.0V, I <sub>D</sub> = 4.0A	1.7	-	-	S
Admittance	Y <sub>fs</sub>   <sup>*6</sup>	Tr2	V <sub>DS</sub> = -5.0V, I <sub>D</sub> = -4.0A	2.0	-	-	3

\*1 Pw  $\leq$  1s, Mounted on a ceramic board (30×30×0.8mm), Limited only by maximum temperature allowed.

\*2 Pw  $\leq 10\mu s$ , Duty cycle  $\leq 1\%$ 

\*3 Tr1:L  $\simeq$  0.1mH, V\_{DD} = 15V, R\_G = 25 $\Omega$ , Starting T\_j = 25°C Fig.1-1,1-2

Tr2: L  $\simeq$  0.1mH, V<sub>DD</sub> = -15V, R<sub>G</sub> = 25 $\Omega$ , Starting T<sub>i</sub> = 25°C Fig.3-1,3-2

\*4 Mounted on a ceramic board (30×30×0.8mm)

\*5 Mounted on a FR4 (25×25×0.8mm)

\*6 Pulsed

### • Electrical characteristics ( $T_a = 25^{\circ}C$ )

<Tr1>

Deremeter	Cump of	Conditions		Values		Linit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	125	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 15V	-	20	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	15	-	
Turn - on delay time	t <sub>d(on)</sub> *5	$V_{DD} \simeq 15$ V, $V_{GS}$ = 10V	-	5.0	-	
Rise time	t <sub>r</sub> *5	I <sub>D</sub> = 2.25A	-	7.5	-	20
Turn - off delay time	t <sub>d(off)</sub> *5	R <sub>L</sub> = 6.67Ω	-	10	-	ns
Fall time	t <sub>f</sub> *5	R <sub>G</sub> = 10Ω	-	3.5	-	

#### <Tr2>

Parameter	Sumbol	Conditions	,	Values		Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	305	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -15V	-	55	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	43	-	
Turn - on delay time	$t_{d(on)}$ *5	$V_{DD} \simeq$ -15V, $V_{GS}$ = -10V	-	7.2	-	
Rise time	t <sub>r</sub> *5	I <sub>D</sub> = -2.25A	-	8.0	-	20
Turn - off delay time	$t_{d(off)}$ *5	R <sub>L</sub> = 6.67Ω	-	28.0	-	ns
Fall time	t <sub>f</sub> *5	R <sub>G</sub> = 10Ω	-	8.5	-	



### • Gate charge characteristics ( $T_a = 25^{\circ}C$ )

### <Tr1>

Deremeter	Cumbal	Symbol Conditions -		Values			Linit
Parameter	Symbol			Min.	Тур.	Max.	Unit
Tatal water all some	<b>O</b> *6		V <sub>GS</sub> = 10V	-	3.0	-	
Total gate charge	Q <sub>g</sub> *6	V <sub>DD</sub> ≃ 15V		-	1.5	-	
Gate - Source charge	Q <sub>gs</sub> *6	I <sub>D</sub> = 4.5A	V <sub>GS</sub> = 4.5V	-	0.6	-	nC
Gate - Drain charge	Q <sub>gd</sub> *6			-	0.5	-	
<tr2></tr2>							•

Parameter	Cumph of	Condi	Values			Linit	
	Symbol	ymbol Conditions		Min.	Тур.	Max.	Unit
Tatal nata abanna	<b>O</b> *6	V <sub>DD</sub> ≃ -15V	V <sub>GS</sub> = -10V	-	6.7	-	
Total gate charge	$Q_g^{*6}$			-	3.4	-	5
Gate - Source charge	${\sf Q}_{\sf gs}{}^{*6}$	I <sub>D</sub> = -4.5A	V <sub>GS</sub> = -4.5V	-	1.1	-	nC
Gate - Drain charge	$Q_{gd}^{*6}$			-	1.3	-	

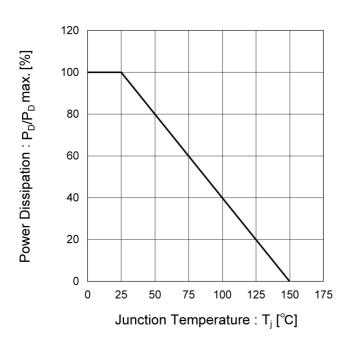
### •Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

<Tr1>

Parameter	Symbol Conditions		Unit			
	Symbol	Conditions	Min.	Тур.	Max.	Unit
Continuous forward current	۱ <sub>s</sub>	$T = 25^{\circ}$	-	-	1.67	^
Pulse forward current	۱ <sub>SP</sub> *2	T <sub>a</sub> = 25°C	-	-	12	A
Forward voltage	$V_{SD}^{*6}$	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.67A	-	-	1.2	V

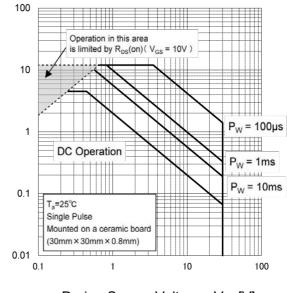
#### <Tr2>

Parameter	Symbol Conditions		,	Unit		
Parameter			Min.	Тур.	Max.	Unit
Continuous forward current	۱ <sub>s</sub>	T - 25°0	-	-	-1.67	^
Pulse forward current	$I_{SP}^{*2}$	T <sub>a</sub> = 25°C	-	-	-12	A
Forward voltage	$V_{SD}^{*6}$	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.67A	-	-	-1.2	V



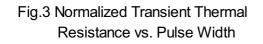
#### Fig.1 Power Dissipation Derating Curve

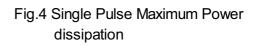
Fig.2 Maximum Safe Operating Area

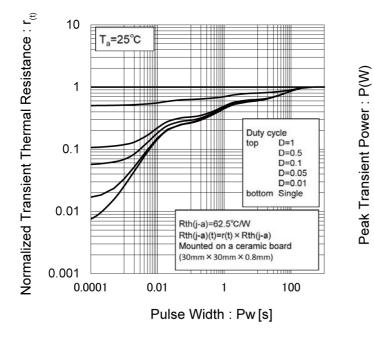


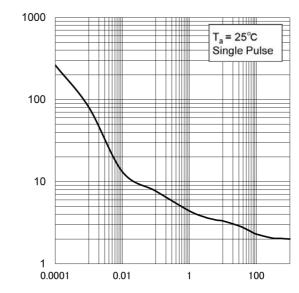
Drain Current : I<sub>D</sub> [A]

Drain - Source Voltage :  $V_{\text{DS}}$  [V]



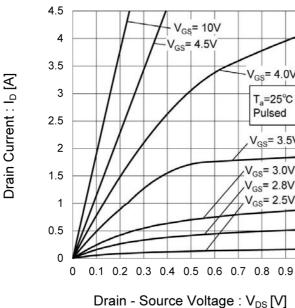






Pulse Width : Pw [s]





### Fig.5 Typical Output Characteristics(I)

V<sub>GS</sub>= 10V

V<sub>GS</sub>= 4.0V

T<sub>a</sub>=25°C Pulsed

V<sub>GS</sub>= 3.5V

V<sub>GS</sub>= 3.0V

V<sub>GS</sub>= 2.8V

V<sub>GS</sub>= 2.5V

1

V<sub>GS</sub>= 4.5V

Fig.6 Typical Output Characteristics(II)

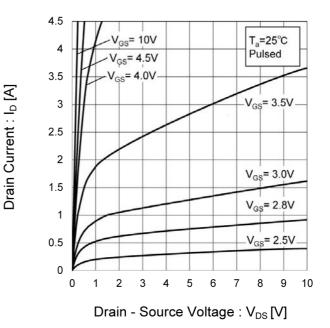
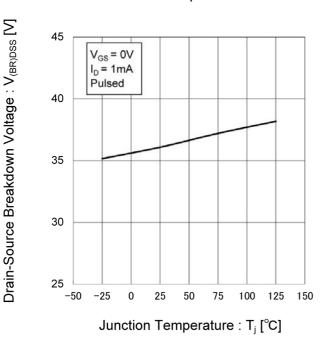
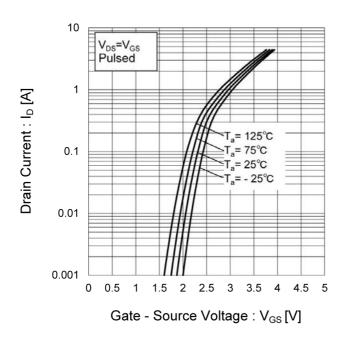


Fig.7 Breakdown Voltage vs. **Junction Temperature** 

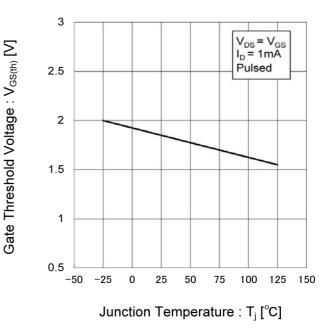






### Fig.8 Typical Transfer Characteristics

Fig.9 Gate Threshold Voltage vs. Junction Temperature



### Fig.10 Forward Transfer Admittance vs. Drain Current

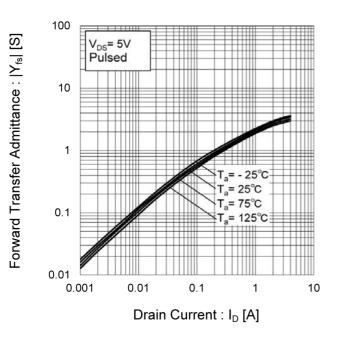




Fig.11 Drain Current Derating Curve

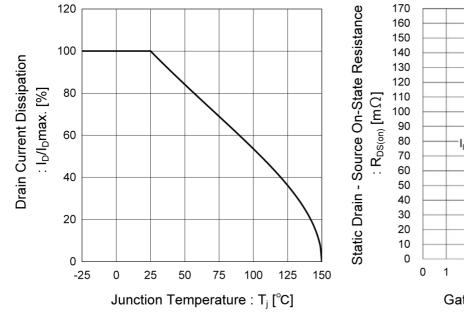


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

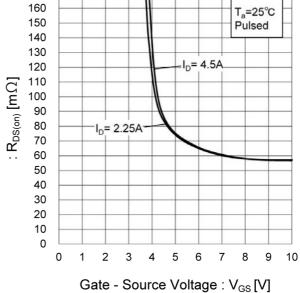
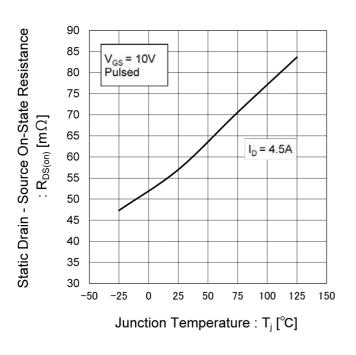


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature







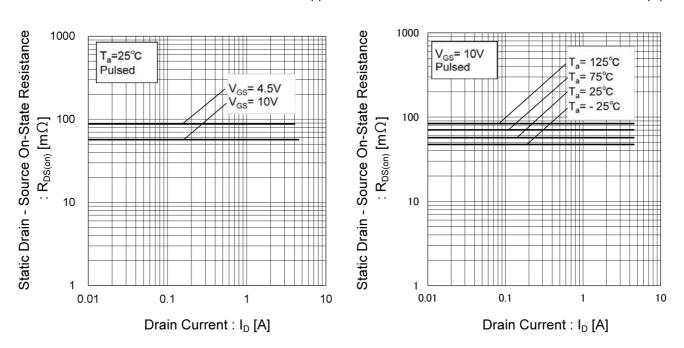


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current (I) Fig.15 Static Drain - Source On - State Resistance vs. Drain Current (II)

Fig.16 Static Drain - Source On - State Resistance vs. Drain Current (III)

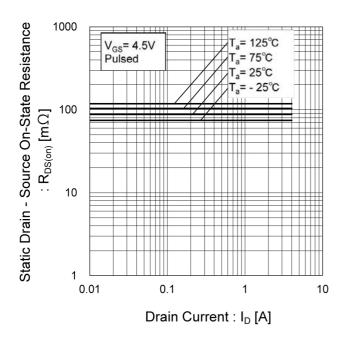




Fig.17 Typical Capacitance vs.

Drain - Source Voltage

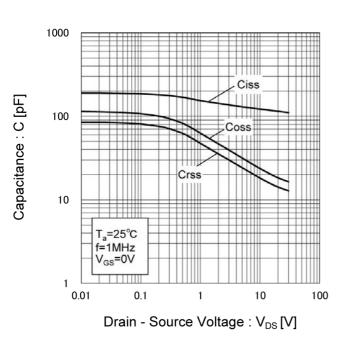


Fig.18 Switching Characteristics

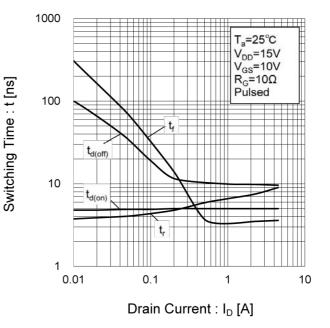


Fig.19 Dynamic Input Characteristics

Gate - Source Voltage : V<sub>GS</sub> [V]

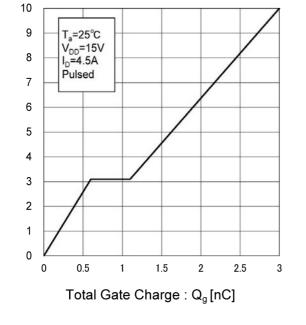
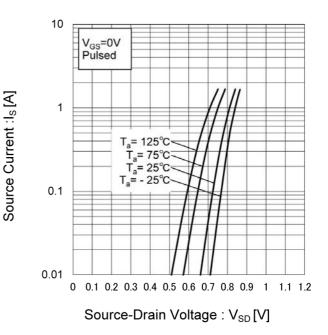
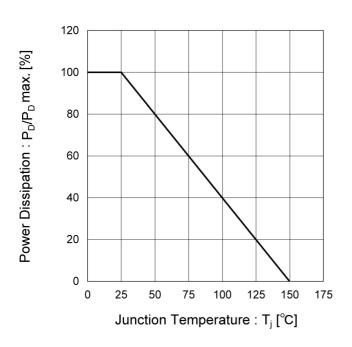


Fig.20 Source Current vs. Source Drain Voltage







#### Fig.1 Power Dissipation Derating Curve

Fig.2 Maximum Safe Operating Area

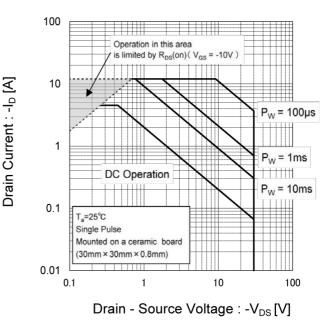
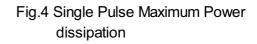
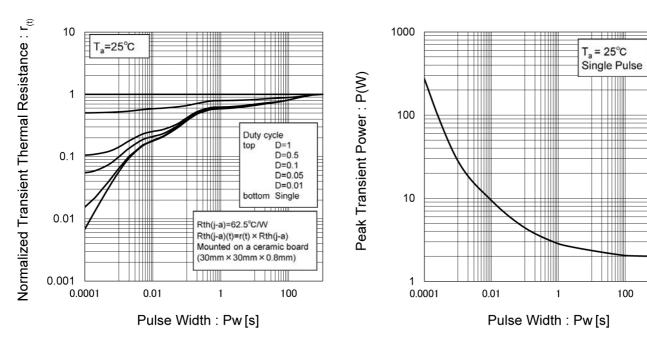


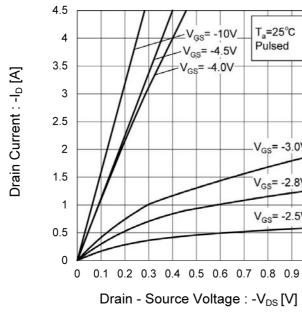
Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width











### Fig.5 Typical Output Characteristics(I)

T<sub>a</sub>=25°C

Pulsed

V<sub>GS</sub>= -3.0V.

V<sub>GS</sub>= -2.8V

V<sub>GS</sub>= -2.5V

1

-10V

Fig.6 Typical Output Characteristics(II)

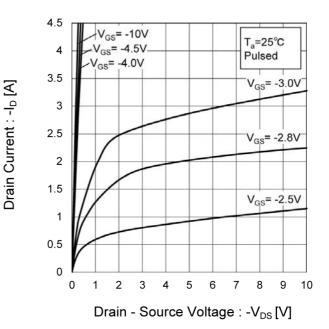
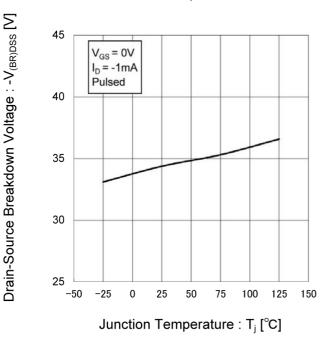
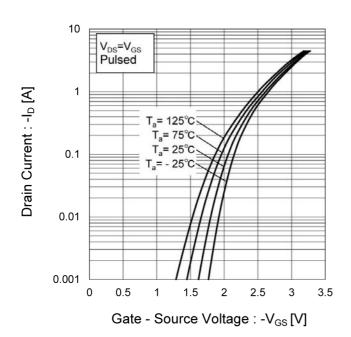


Fig.7 Breakdown Voltage vs. **Junction Temperature** 

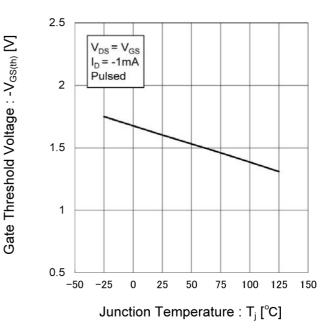




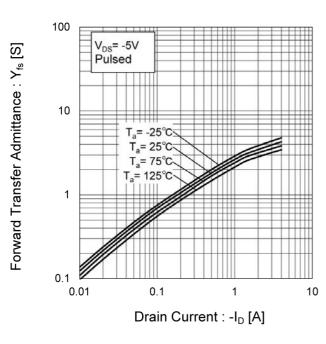


### Fig.8 Typical Transfer Characteristics

Fig.9 Gate Threshold Voltage vs. Junction Temperature



### Fig.10 Forward Transfer Admittance vs. Drain Current





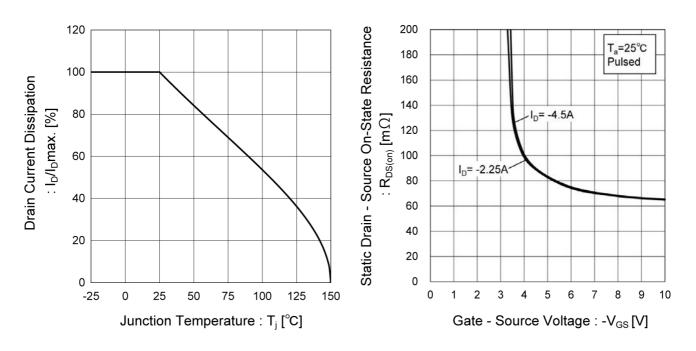
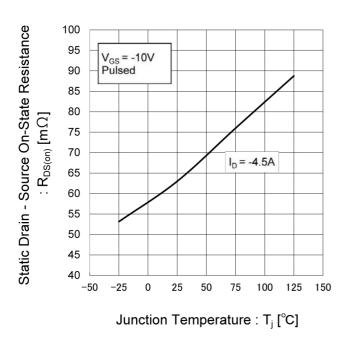


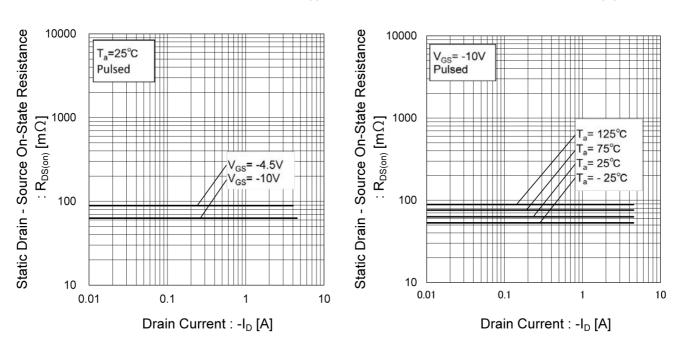
Fig.11 Drain Current Derating Curve

#### Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

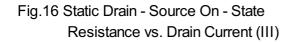


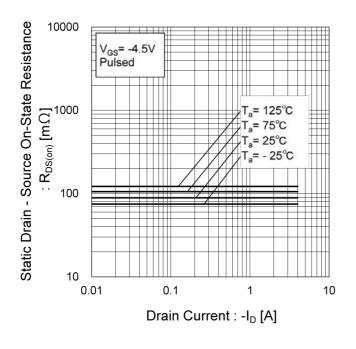




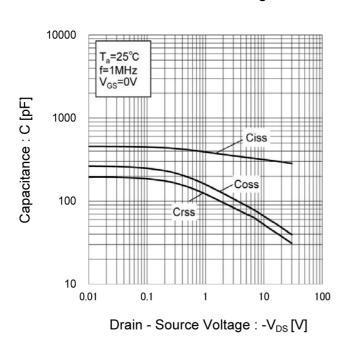
#### Fig.14 Static Drain - Source On - State Resistance vs. Drain Current (I)

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)









#### Fig.17 Typical Capacitance vs. Drain - Source Voltage

Fig.18 Switching Characteristics

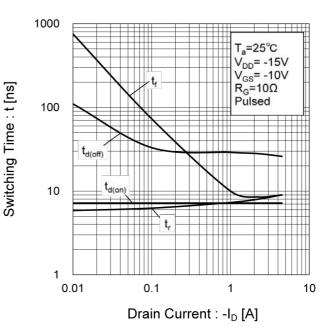


Fig.19 Dynamic Input Characteristics

Gate - Source Voltage : -V<sub>GS</sub> [V]

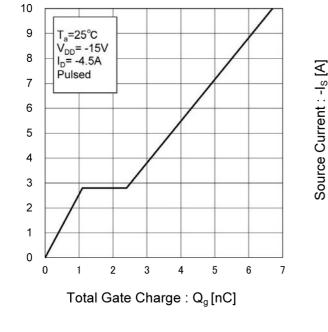
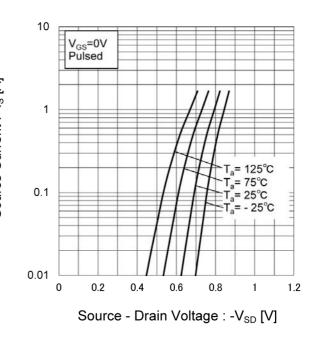


Fig.20 Source Current vs. Source Drain Voltage





### Measurement circuits <Tr1>

Fig.1-1 Switching Time Measurement Circuit

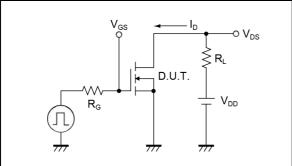


Fig.2-1 Gate Charge Measurement Circuit

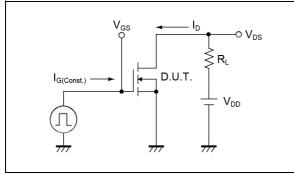


Fig.3-1 Avalanche Measurement Circuit

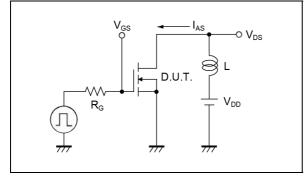
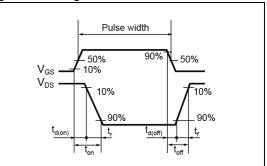
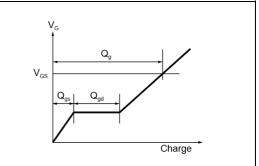


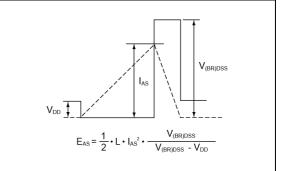
Fig.1-2 Switching Waveforms



#### Fig.2-2 Gate Charge Waveform



#### Fig.3-2 Avalanche Waveform





### Measurement circuits <Tr2>

Fig.4-1 Switching Time Measurement Circuit

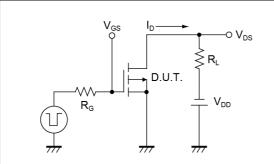


Fig.5-1 Gate Charge Measurement Circuit

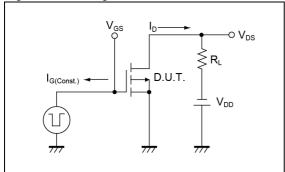


Fig.6-1 Avalanche Measurement Circuit

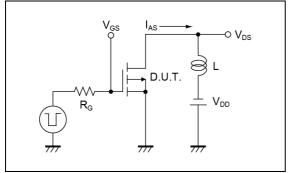
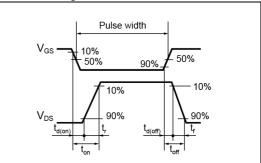
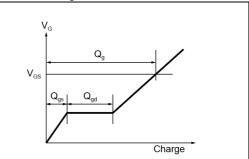


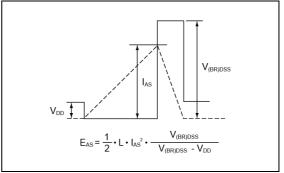
Fig.4-2 Switching Waveforms







#### Fig.6-2 Avalanche Waveform

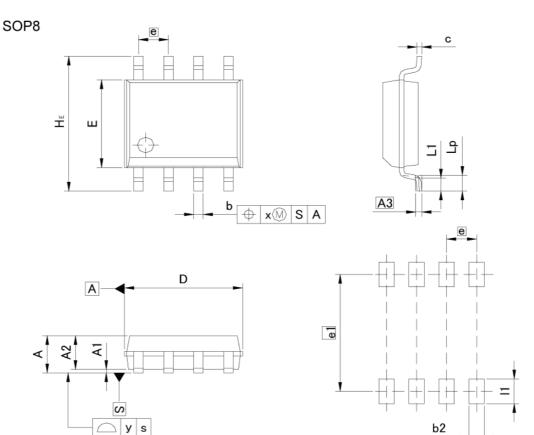


#### Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.



#### Dimensions



Pattern of terminal position areas [Not a pattern of soldering pads]

DIM	MILIM	ETERS	INC	HES
	MIN	MAX	MIN	MAX
A	<u>-</u> 2	1.75	-	0.069
A1	0.	15	0.0	06
A2	1.40	1.60	0.055	0.063
A3	0.	25	0.0	10
b	0.30	0.50	0.012	0.020
с	0.10	0.30	0.004	0.012
D	4.80	5.20	0.189	0.205
E	3.75	4.05	0.148	0.159
е	1.	27	0.0	50
HE	5.70	6.30	0.224	0.248
L1	0.40	0.60	0.016	0.024
Lp	0.65	0.85	0.026	0.033
x	0.	15	0.0	06
У	0.	10	0.0	04

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2		0.65	<del></del>	0.026
e1	5.15		0.203	
11	<del></del>	1.15	<b>2</b> 76	0.045

Dimension in mm/inches



# Notice

#### Precaution on using ROHM Products

1. Our Products are designed and manufactured for application in ordinary electronic equipments (such as AV equipment, OA equipment, telecommunication equipment, home electronic appliances, amusement equipment, etc.). If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment <sup>(Note 1)</sup>, transport equipment, traffic equipment, aircraft/spacecraft, nuclear power controllers, fuel controllers, car equipment including car accessories, safety devices, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

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- 2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:
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  - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
  - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
  - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

#### Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

#### Precautions Regarding Application Examples and External Circuits

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- 2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

#### **Precaution for Electrostatic**

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

#### **Precaution for Storage / Transportation**

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

#### **Precaution for Product Label**

A two-dimensional barcode printed on ROHM Products label is for ROHM's internal use only.

#### **Precaution for Disposition**

When disposing Products please dispose them properly using an authorized industry waste company.

#### Precaution for Foreign Exchange and Foreign Trade act

Since concerned goods might be fallen under listed items of export control prescribed by Foreign exchange and Foreign trade act, please consult with ROHM in case of export.

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